Performance

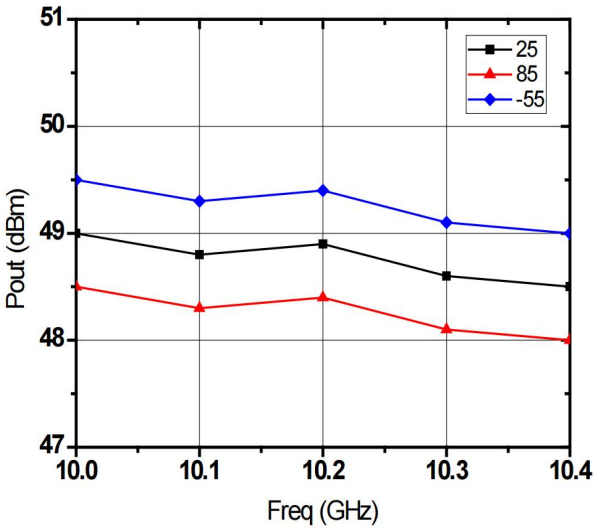
- Technology: 0.25um Power GaN HEMT
- Frequency: 10~10.4GHz
- Typical Pout : 48dBm(CW)
- Typical Gain: 7.5dB
- Typical PAE: 32%
- Bias: 28V/-2.6V
- Package: Metal Ceramic

Electrical Specifications (TA=25℃,Vd=28V,Vg=-2.6V,F:10~10.4GHz)

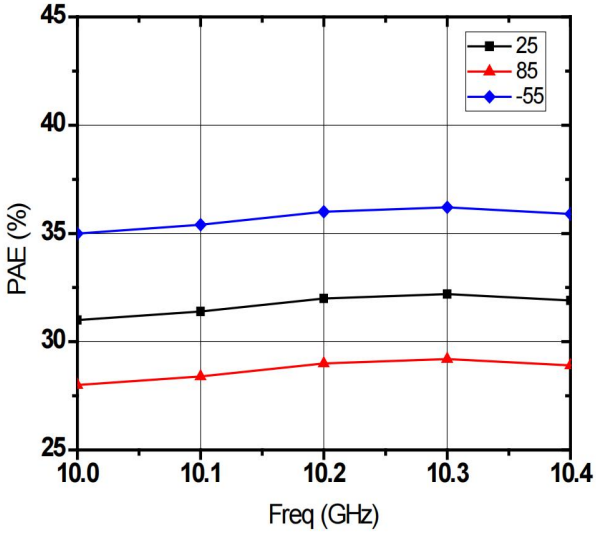
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	48	-	dBm
Gp	Power Gain	-	7.5	-	dB
ηadd	Power Added Efficiency	-	32	-	%
△Gp	Gain Flatness	-0.6	-	+0.6	dB

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

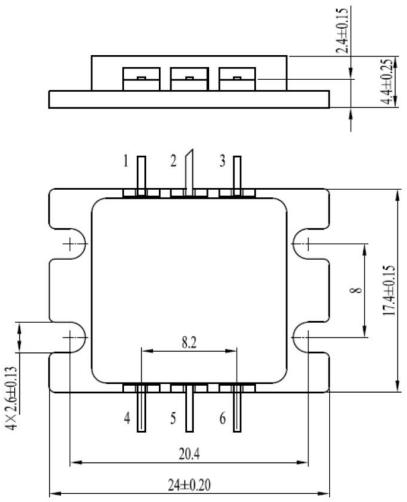


Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	180W	25℃
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

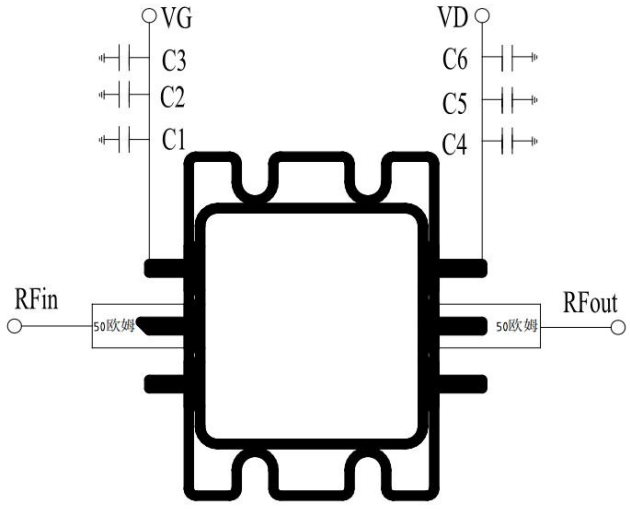
Outline Drawing



Pad Definition

No	Function	No	Function
1、3	Vg	4、6	Vd
2	RFin	5	RFout

Application Circuit



Note:

(1) The typical packaging form is C164-2 shell package;

(2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;

(3) In order to ensure the good performance of the power module, the power filter and energy storage capacitor should be reasonably selected according to the modulation mode during pulse operation

the capacity value;

(4) Recommended values for signal source modulation: C1=C4=100pf, C2=C5=1000pf, C3=47uf, C6=100uf; drain

Modulation recommended value: C1=C4=100pf, C2=C5=1000pf, C3=47uf, no C6.